

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT3090L is a Low $V_{CE(SAT)}$ NPN Transistor in a space saving Power SOT-23F surface mount package, designed for DC-DC converters for mobile systems and LAN cards, motor control, power management and strobe flash units.

Marking code is 309L.

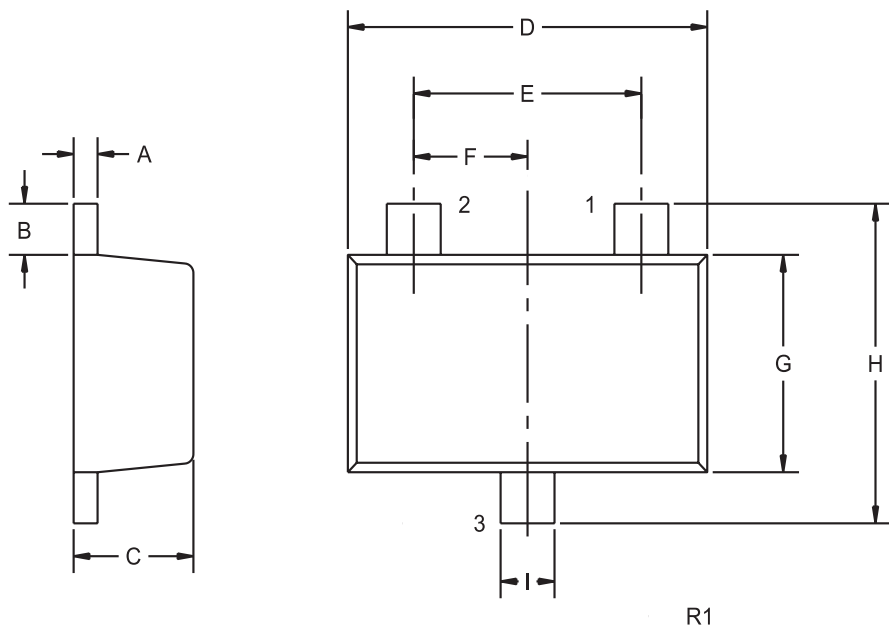
MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	45	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Continuous Collector Current	I_C	5.0	A
Peak Pulse Current	I_{CM}	10	A
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=20\text{V}$			100	nA
I_{EBO}	$V_{EB}=5.0\text{V}$			100	nA
BV_{CBO}	$I_C=10\mu\text{A}$	45			V
BV_{CEO}	$I_C=10\text{mA}$	15			V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0			V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=1.0\text{mA}$		30	50	mV
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=20\text{mA}$		60	150	mV
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$		85	200	mV
$V_{CE(SAT)}$	$I_C=3.0\text{A}, I_B=60\text{mA}$		145	300	mV
h_{FE}	$V_{CE}=2.0\text{V}, I_C=500\text{mA}$	200			
h_{FE}	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$	200			
h_{FE}	$V_{CE}=2.0\text{V}, I_C=3.0\text{A}$	175			
h_{FE}	$V_{CE}=2.0\text{V}, I_C=5.0\text{A}$	150			
C_{ob}	$V_{CB}=10\text{V}, f=1.0\text{MHz}$			100	pF
f_T	$V_{CE}=10\text{V}, I_C=500\text{mA}$	100			MHz

SOT-23F CASE - MECHANICAL OUTLINE



R1

LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.012	0.020	0.30	0.50
C	0.031	0.039	0.80	1.00
D	0.110	0.118	2.80	3.00
E	0.075		1.90	
F	0.037		0.95	
G	0.059	0.067	1.50	1.70
H	0.091	0.098	2.30	2.50
I	0.014	0.018	0.35	0.45

SOT-23F (REV: R1)

R0 (13-December 2001)